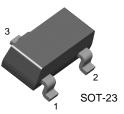
FAIRCHILD

SEMICONDUCTOR®

KST2222A

General Purpose Transistor



1. Base 2. Emitter 3. Collector

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_a=25°C unless otherwise noted

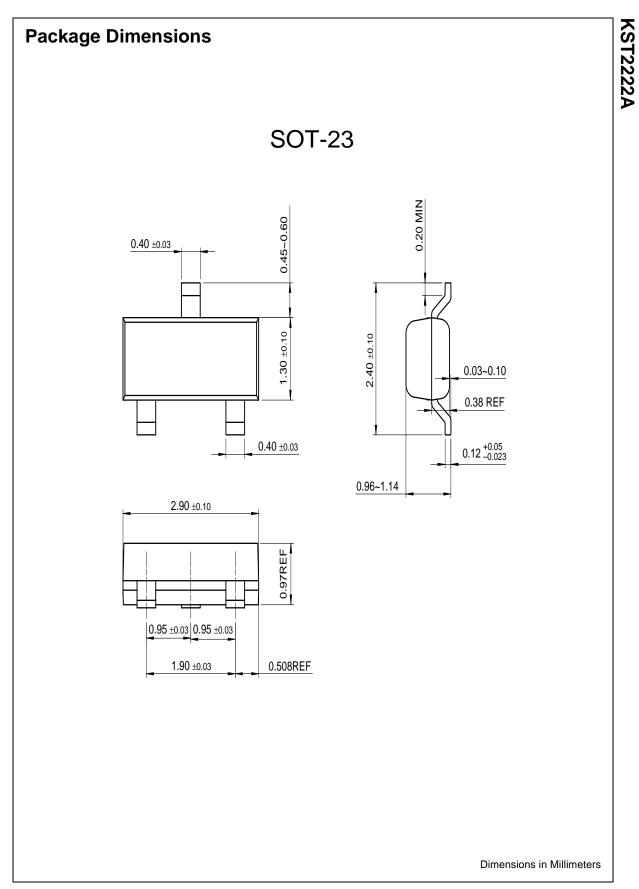
Symbol	Parameter	Value	Units	
V _{CBO}	Collector-Base Voltage	75	V	
V _{CEO}	Collector-Emitter Voltage	40	V	
V _{EBO}	Emitter-Base Voltage	6	V	
c	Collector Current	600	mA	
P _C	Collector Power Dissipation	350	mW	
Т _{STG}	Storage Temperature	150	°C	

Electrical Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	I _C =10μA, I _E =0	75		V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C =10mA, I _B =0	40		V
BV_{EBO}	Emitter-Base Breakdown Voltage	I _E =10μA, I _C =0	6		V
I _{CBO}	Collector Cut-off Current	V _{CB} =60V, I _E =0		0.01	μΑ
h _{FE}	* DC Current Gain	$V_{CE}=10V, I_{C}=0.1mA \\ V_{CE}=10V, I_{C}=1mA \\ V_{CE}=10V, I_{C}=10mA \\ V_{CE}=10V, I_{C}=150mA \\ V_{CE}=10V, I_{C}=500mA \\ \label{eq:central_constraint}$	35 50 75 100 40	300	
V _{CE} (sat)	* Collector-Emitter Saturation Voltage	I _C =150mA, I _B =15mA I _C =500mA, I _B =50mA		0.3 1.0	V V
V _{BE} (sat)	* Base-Emitter Saturation Voltage	I _C =150mA, I _B =15mA I _C =500mA, I _B =50mA	0.6	1.2 2.0	V V
f _T	Current Gain Bandwidth Product	I _C =20mA, V _{CE} =20V, f=100MHz	300		MHz
C _{ob}	Output Capacitance	V _{CB} =10V, I _E =0, f=1MHz		8	pF
NF	Noise Figure	I _C =100μA, V _{CE} =10V R _S =1KΩ, f=1MHz		4	dB
t _{ON}	Turn On Time	V _{CC} =30V, I _C =150mA V _{BE} =0.5V, I _{B1} =15mA		35	ns
t _{OFF}	Turn Off Time	V _{CC} =30V, I _C =150mA I _{B1} =I _{B2} =15mA		285	ns

* Pulse Test: PW≤300µs, Duty Cycle≤2%





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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
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